Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- · Low threshold voltage
- · Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- AEC-Q101 qualified

3. Applications

- · Relay driver
- · High-speed line driver
- · High-side loadswitch
- · Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V	
V_{GS}	gate-source voltage			-12	-	12	V	
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-	-2.4	Α	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 25 °C		-	97	128	mΩ	

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D
2	S	source		
3	D	drain	TO-236AB (SOT23)	G S S 017aaa259

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV100XPEA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMV100XPEA	DP%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-2.4	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.5	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-10	Α
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$T_{j(init)}$ = 25 °C; I_D = -0.5 A; DUT in avalanche (unclamped)		-	5	mJ
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	463	mW
			[1]	-	1.06	W
		T _{sp} = 25 °C		-	4.45	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain d	liode				'	,
I _S	source current	T _{amb} = 25 °C	[1]	-	-1	Α
ESD maximum	rating					
V _{ESD}	electrostatic discharge voltage	НВМ	[3]	-	2000	V

Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. Measured between all pins.

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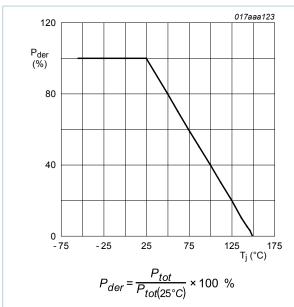


Fig. 1. Normalized total power dissipation as a function of junction temperature

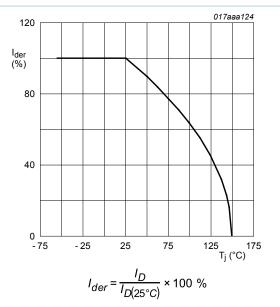
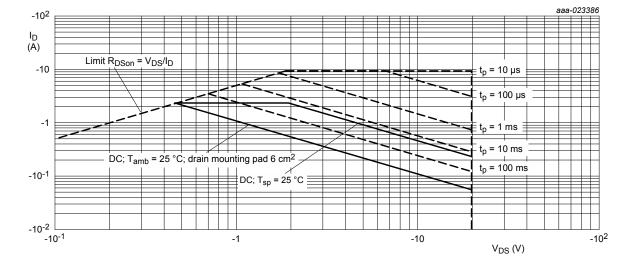


Fig. 2. Normalized continuous drain current as a function of junction temperature



I_{DM} = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient		[1]	-	226	270	K/W
			[2]	_	98	118	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	28	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

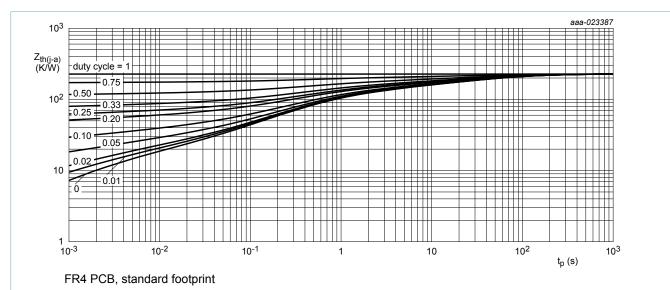


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

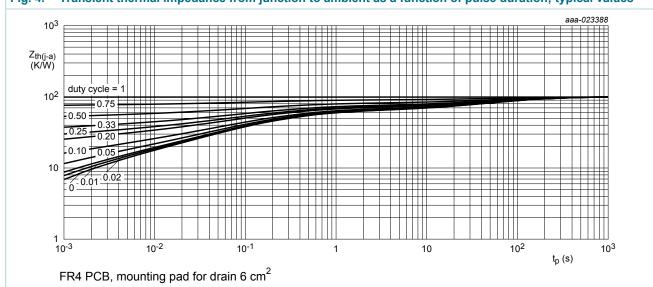


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

	Conditions	Min	Тур	Max	Unit
eristics					
drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.75	-1	-1.25	V
drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μΑ
	V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
	V _{GS} = 4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	2	μΑ
	V _{GS} = -4.5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-2	μΑ
drain-source on-state	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 25 °C	-	97	128	mΩ
resistance	V_{GS} = -4.5 V; I_D = -2.4 A; T_j = 150 °C	-	142	187	mΩ
	V_{GS} = -2.5 V; I_D = -1.9 A; T_j = 25 °C	-	147	210	mΩ
forward transconductance	V_{DS} = -10 V; I_D = -2.4 A; T_j = 25 °C	-	6	-	S
gate resistance	f = 1 MHz	-	17.4	-	Ω
acteristics		•			
total gate charge	V_{DS} = -10 V; I_{D} = -2.4 A; V_{GS} = -4.5 V;	-	3.4	6	nC
gate-source charge	T _j = 25 °C	-	0.85	-	nC
gate-drain charge		-	0.75	-	nC
input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	386	-	pF
output capacitance	T _j = 25 °C	-	54	-	pF
reverse transfer capacitance		-	40	-	pF
turn-on delay time	V_{DS} = -10 V; I_{D} = -2.4 A; V_{GS} = -4.5 V;	-	5	-	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4	-	ns
turn-off delay time		-	35	-	ns
fall time		-	17	-	ns
diode		1			,
source-drain voltage	I _S = -1 A; V _{GS} = 0 V; T _i = 25 °C	_	-0.7	-1.2	V
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current drain-source on-state resistance forward transconductance gate resistance racteristics total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

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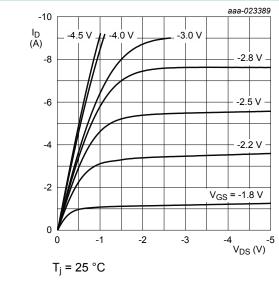


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

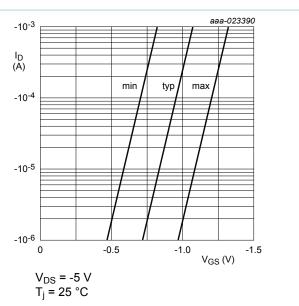


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

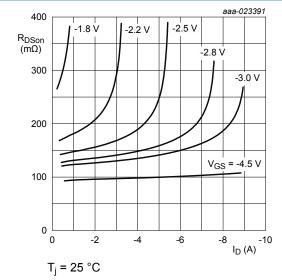


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

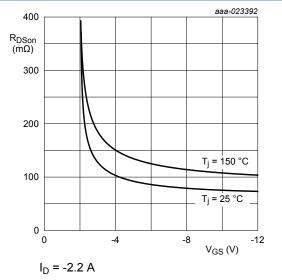


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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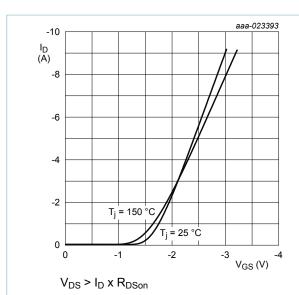


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

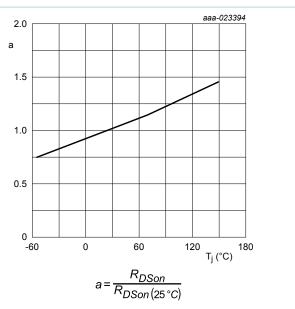


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

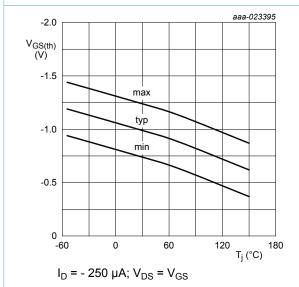
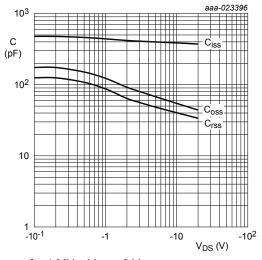


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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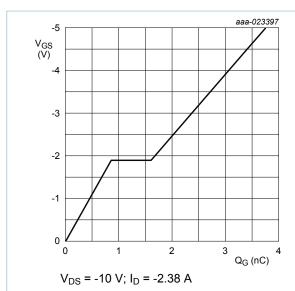


Fig. 14. Gate-source voltage as a function of gate charge; typical values

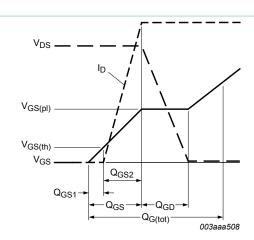


Fig. 15. Gate charge waveform definitions

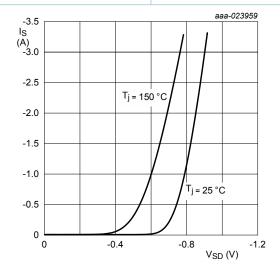
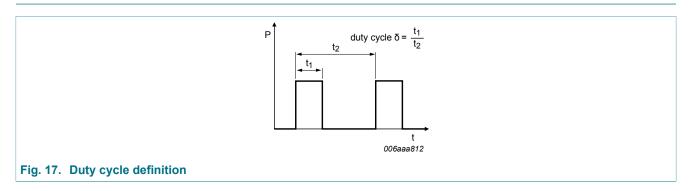


Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

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11. Test information



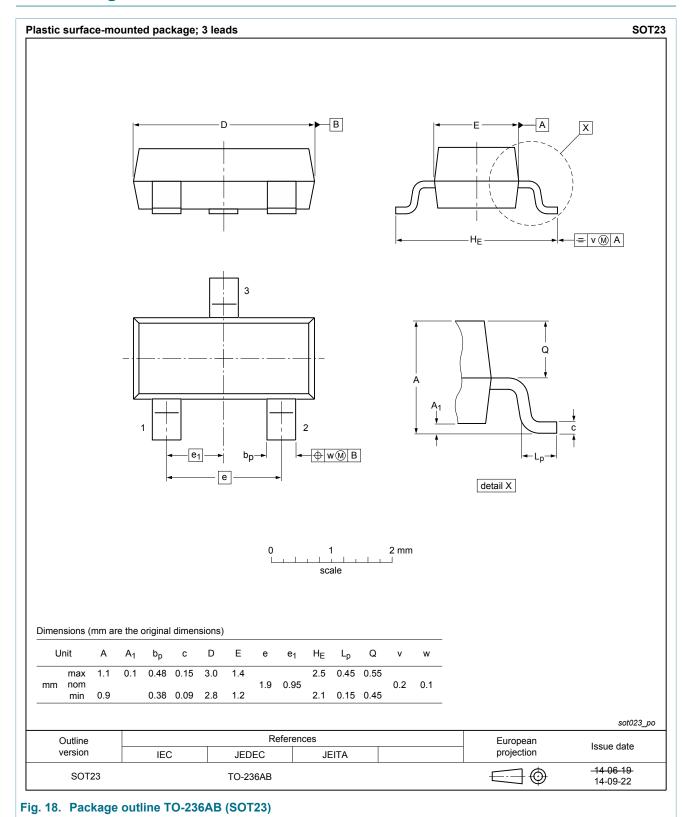
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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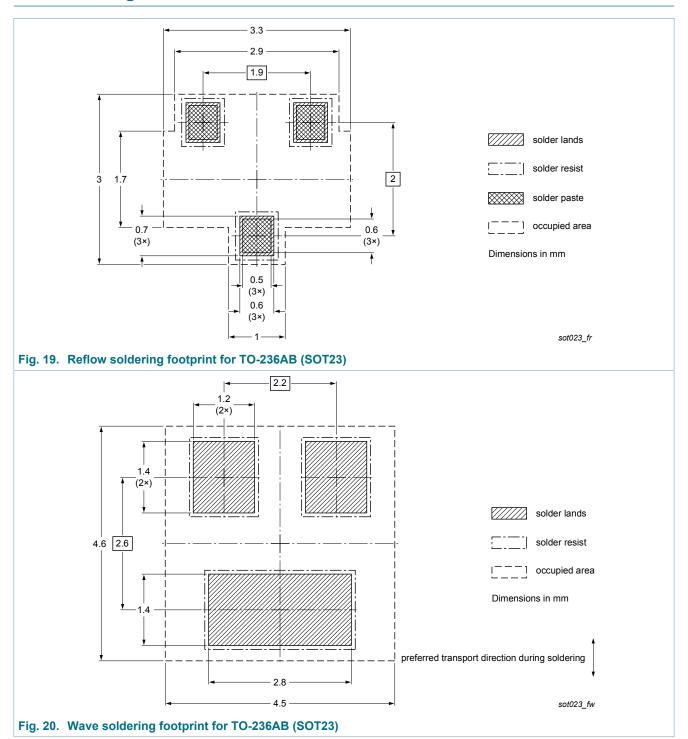
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

- table of the fine terms of the first of th							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PMV100XPEA v.2	20170615	Product data sheet	-	PMV100XPEA v.1			
Modification:	Figure 1 removed						
PMV100XPEA v.1	20160630		-	-			

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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